

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current	Steady State	T _A = +25°C (Note 6)	I _D	-0.67	A
		T _A = +85°C (Note 6)		-0.48	
		T _A = +25°C (Note 5)		-0.53	
Pulsed Drain Current (Note 7)			I _{DM}	2.5	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P _D	0.45	W
	(Note 6)		0.71	W
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	275	°C/W
	(Note 6)		177	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

- Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
7. Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%.

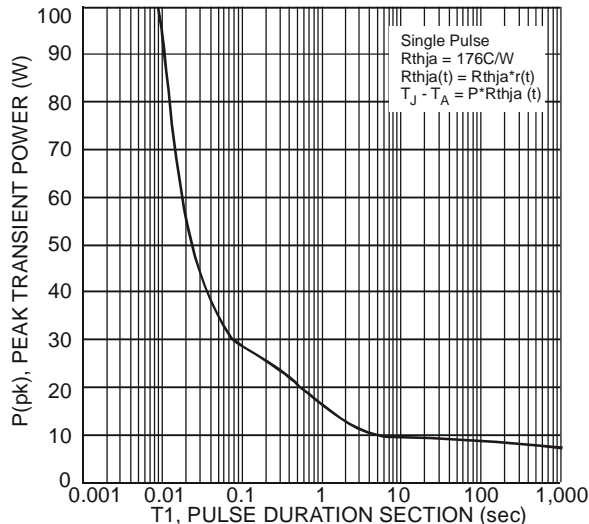


Fig. 1 Single Maximum Power Dissipation

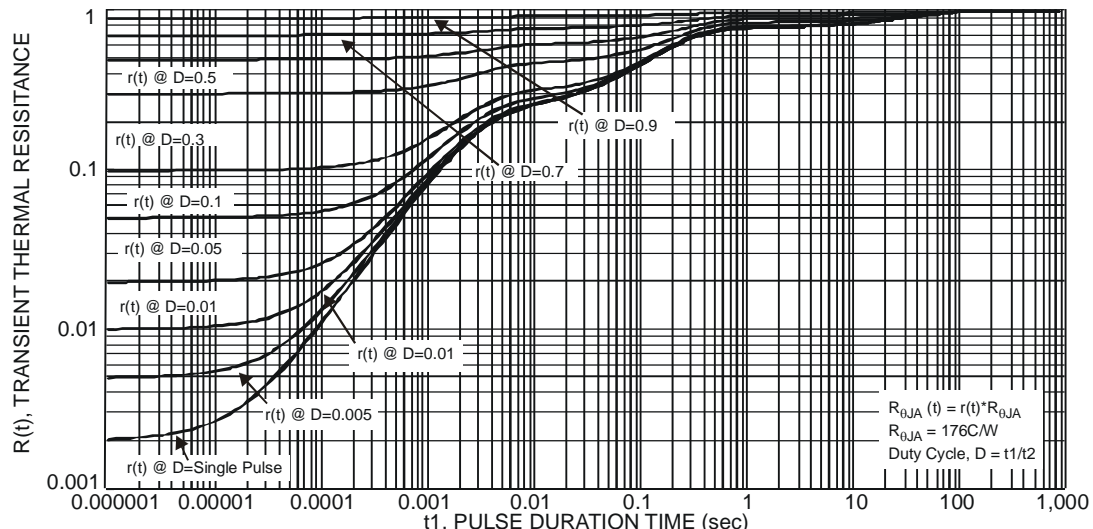


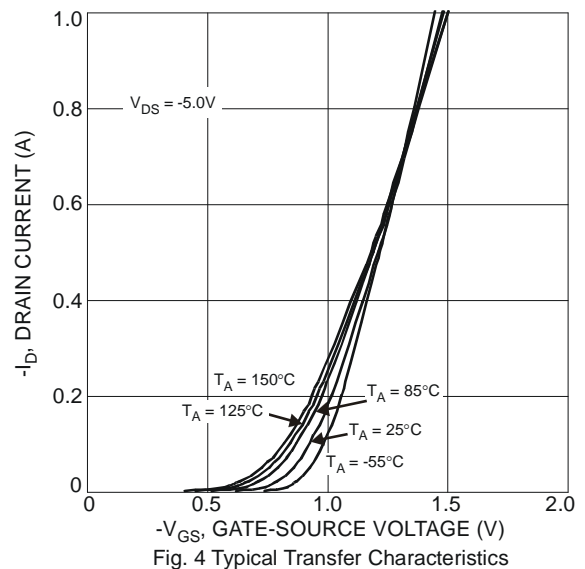
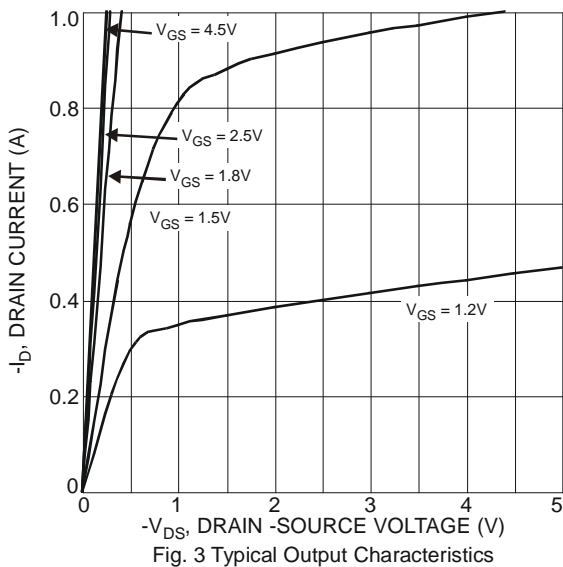
Fig. 2 Transient Thermal Resistance

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current $T_J = 25^\circ\text{C}$	I_{DSS}	—	—	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 3	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.5	—	-1.1	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	1	Ω	$V_{GS} = -4.5V, I_D = -400mA$
				1.5		$V_{GS} = -2.5V, I_D = -200mA$
				2		$V_{GS} = -1.8V, I_D = -100mA$
Forward Transfer Admittance	$ Y_{FS} $	50	—	—	mS	$V_{DS} = -3V, I_D = -300mA$
Diode Forward Voltage	V_{SD}	—	—	-1.2	V	$V_{GS} = 0V, I_S = -300mA$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{ISS}	—	76	150	pF	$V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz$
Output Capacitance	C_{OSS}	—	9	—	pF	
Reverse Transfer Capacitance	C_{RSS}	—	6.43	—	pF	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Gate Resistance	R_G	—	167	—	Ω	
Total Gate Charge	Q_G	—	0.9	—	nC	$V_{GS} = -4.5V, V_{DS} = -15V, I_D = -1A$
Total Gate Charge	Q_G	—	1.5	—	nC	
Gate-Source Charge	Q_{GS}	—	0.1	—	nC	$V_{GS} = -8V, V_{DS} = -15V, I_D = -1A$
Gate-Drain Charge	Q_{GD}	—	0.2	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.0	—	ns	$V_{DD} = -10V, R_L = 10\Omega, V_{GS} = -4.5V, R_G = 6\Omega$
Turn-On Rise Time	t_R	—	5.9	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	35.7	—	ns	
Turn-Off Fall Time	t_F	—	16.7	—	ns	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

Typical Electrical Characteristics



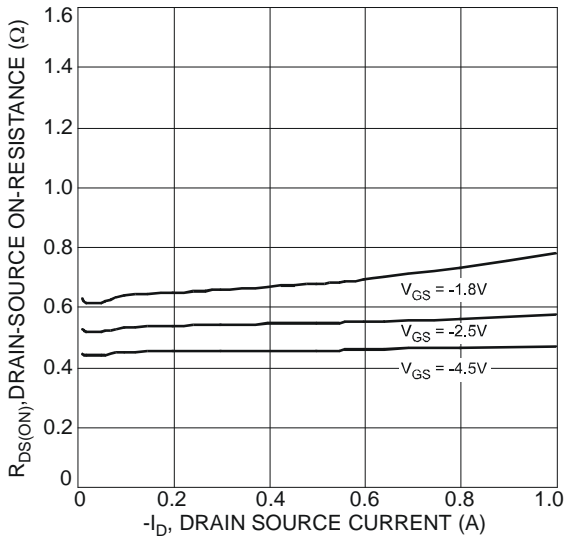


Fig. 5 Typical On-Resistance vs. Drain Current and Gate Voltage

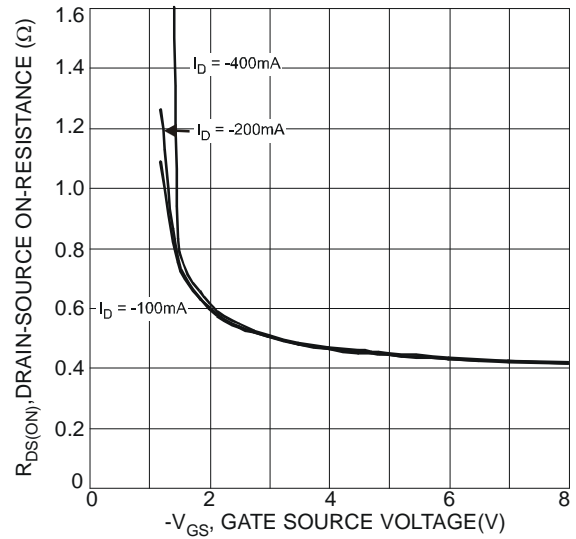


Fig. 6 Typical On-Resistance vs. Drain Current and Gate Voltage

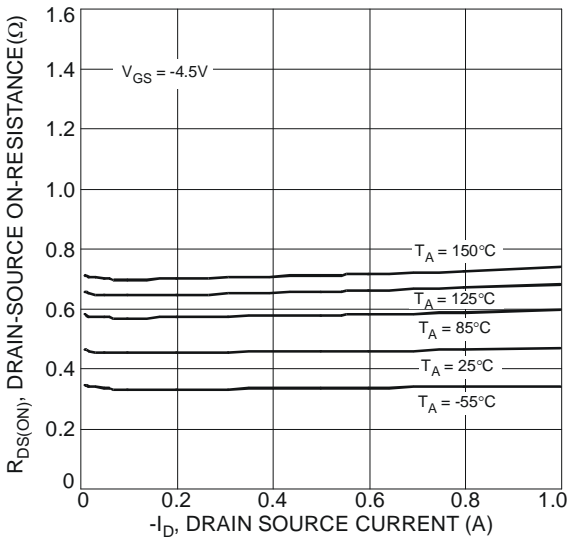


Fig. 7 Typical On-Resistance vs. Drain Current and Temperature

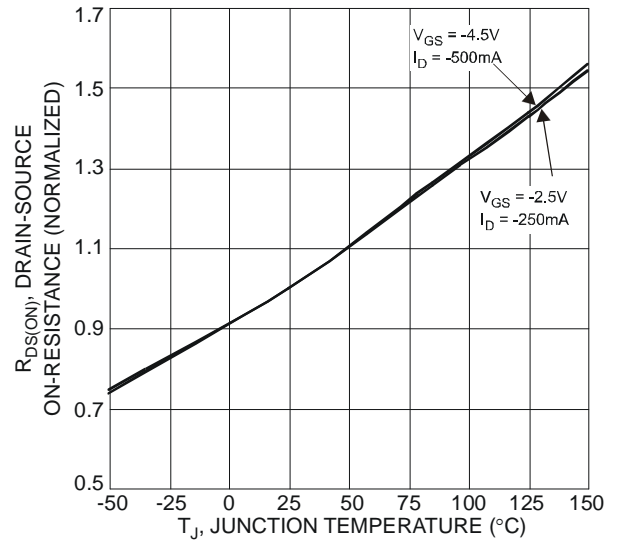


Fig. 8 On-Resistance Variation with Temperature

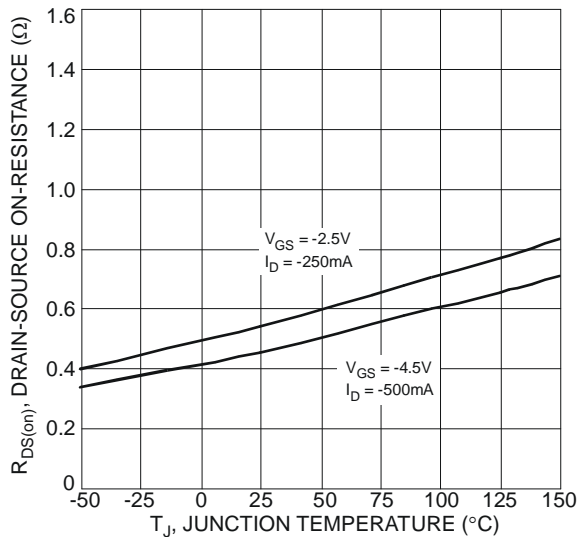


Fig. 9 On-Resistance Variation with Temperature

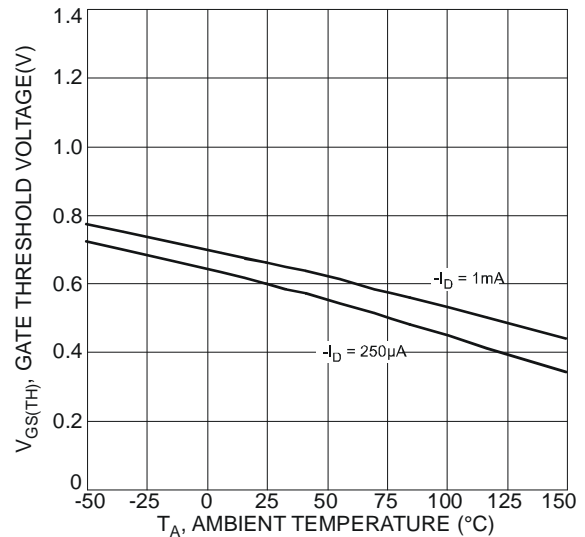


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

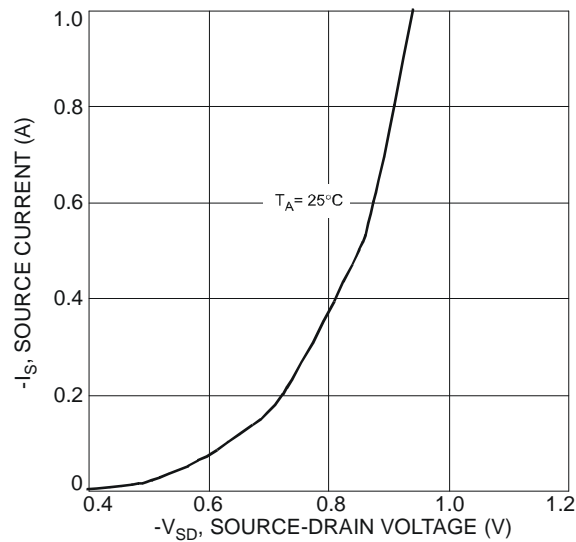


Fig. 11 Diode Forward Voltage vs. Current

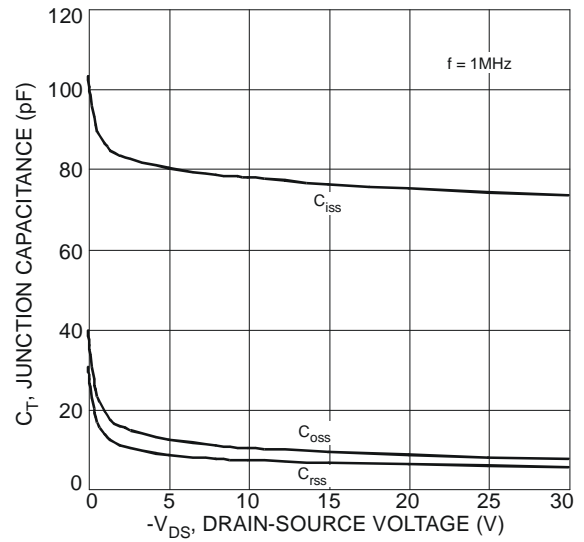


Fig. 12 Typical Junction Capacitance

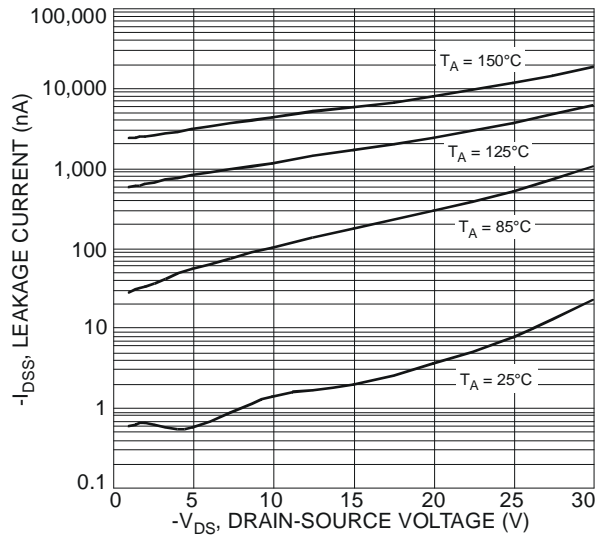


Fig. 13 Typical Drain-Source Leakage Current vs. Voltage

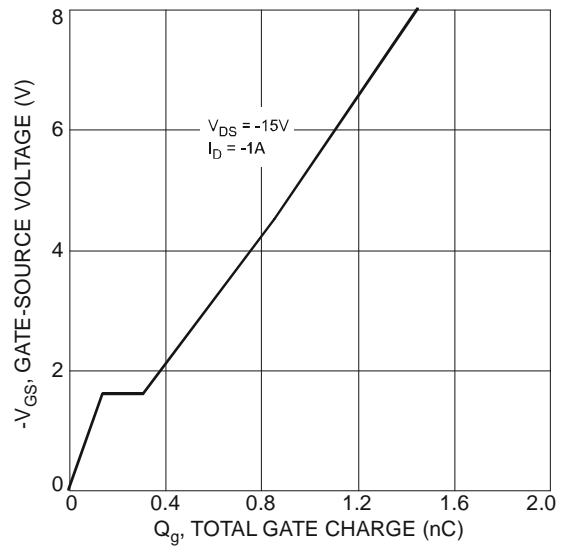
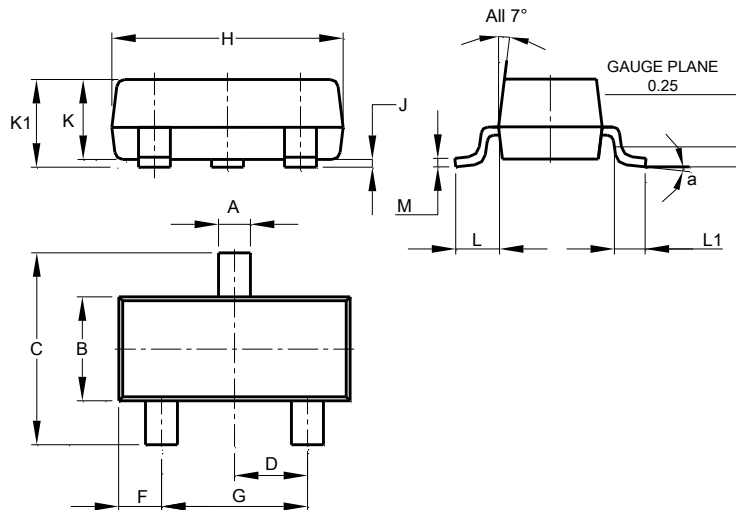


Fig. 14 Gate-Charge Characteristics

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

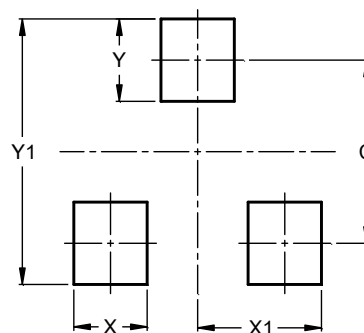


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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